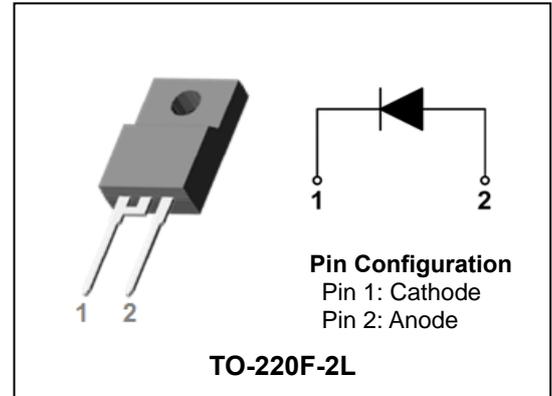# DUAL COMMON CATHODE SCHOTTKY RECTIFIER

Features

- Low forward voltage drop
- Low power loss and High efficiency
- Low leakage current
- High surge capability
- Full lead (Pb)-free and RoHS compliant device

Applications

- Power supply - Output rectification
- Converter
- Free-wheeling diode
- Reverse battery protection
- Power inverters

Pin Configuration
Pin 1: Cathode
Pin 2: Anode

TO-220F-2L

Product Characteristics

$I_{F(AV)}$	5A
V_{RRM}	200V
V_{FM} at 125℃	0.72V (Typ.)
I_{FSM}	120A

Description

The SDB5200PH has two schottky barriers arranged in a common cathode configuration. Typical applications are in switching power supplies, converters, free-wheeling diodes, and reverse battery protection.
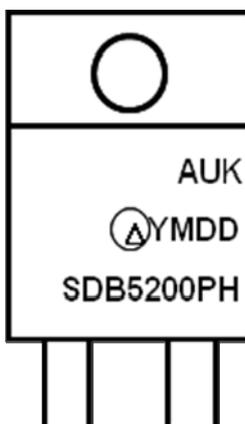
Ordering Information

Device	Marking Code	Package	Packaging
SDB5200PH	SDB5200PH	TO-220F-2L	Tube

Marking Information

AUK = Manufacture Logo

Δ = Control Code of Manufacture

YMDD = Date Code Marking

  -. Y = Year Code

  -. M = Monthly Code

  -. DD = Daily Code

SDB5200PH = Specific Device Code

Absolute Maximum Ratings (Limiting Values)

Characteristic	Symbol	Value	Unit
Maximum repetitive reverse voltage Maximum working peak reverse voltage Maximum DC blocking voltage	V_{RRM} V_{RWM} V_R	200	V
Maximum average forward rectified current	$I_{F(AV)}$	5	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode	I_{FSM}	120	A
Storage temperature range	T_{stg}	-45℃ to +150℃	℃
Maximum operating junction temperature	T_j	150	℃

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Maximum thermal resistance junction to case	$R_{th(j-c)}$	4.0	℃/W

Electrical Characteristics (Per Diode)

Characteristic	Symbol	Test Condition		Min.	Typ.	Max.	Unit
Peak forward voltage drop	V_{FM} [1]	I_{FM} = 5A	T_j=25℃	-	0.85	0.95	V
			T_j=125℃	-	0.72	0.76	V
Reverse leakage current	I_{RM} [1]	$V_R = V_{RRM}$	T_j=25℃	-	-	10	uA
			T_j=125℃	-	-	10	mA
Junction capacitance	C_j	$V_R = 1V_{DC}$, f=1MHz		-	150	-	pF

Note : (1) Pulse test : $t_P \leq 380 \mu s$, Duty cycle $\leq 2\%$

To evaluate the conduction losses use the following equation: $P_F = 0.68\ I_{F(AV)} + 0.032\ I_F^2{}_{(RMS)}$
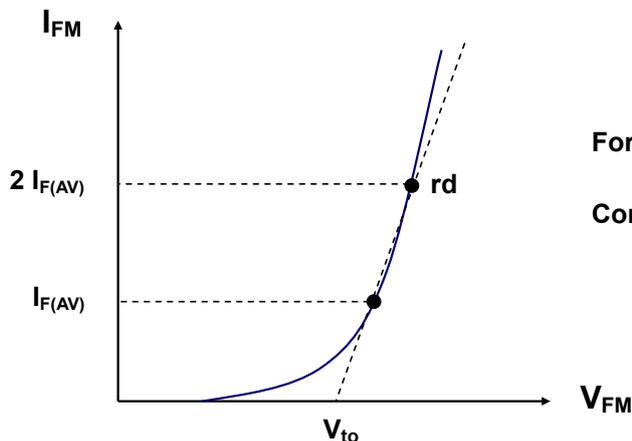
Forward Voltage : $V_{FM} = V_{to} + rd\ I_{FM}$

Conduction Loss : $P_F = V_{to}\ I_{F(AV)} + rd\ I_F^2{}_{(RMS)}$

Rating and Characteristic Curves
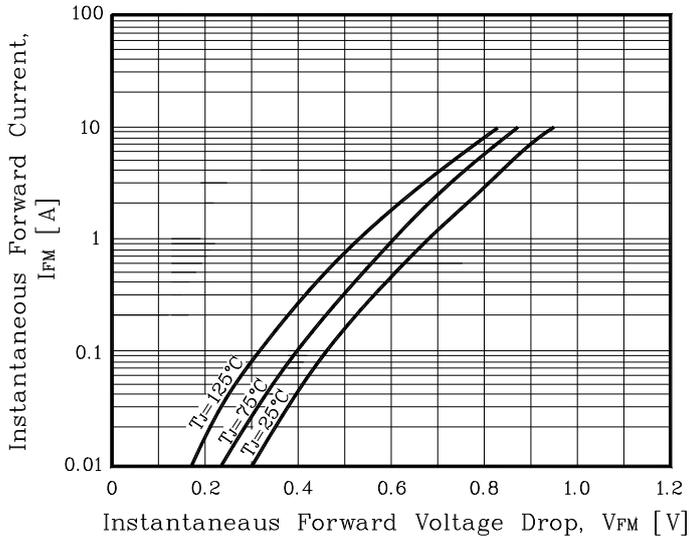
Fig. 1) Typical Forward Characteristics

Instantaneous Forward Current, I_{FM} [A] vs Instantaneous Forward Voltage Drop, V_{FM} [V]

$T_J=125°C$
$T_J=75°C$
$T_J=25°C$

Fig. 2) Typical Reverse Characteristics

Instantaneous Reverse Leakage Current, I_{RM} [μA] vs Instantaneous Reverse Voltage, V_R [V]

$T_J=125°C$
$T_J=75°C$
$T_J=25°C$
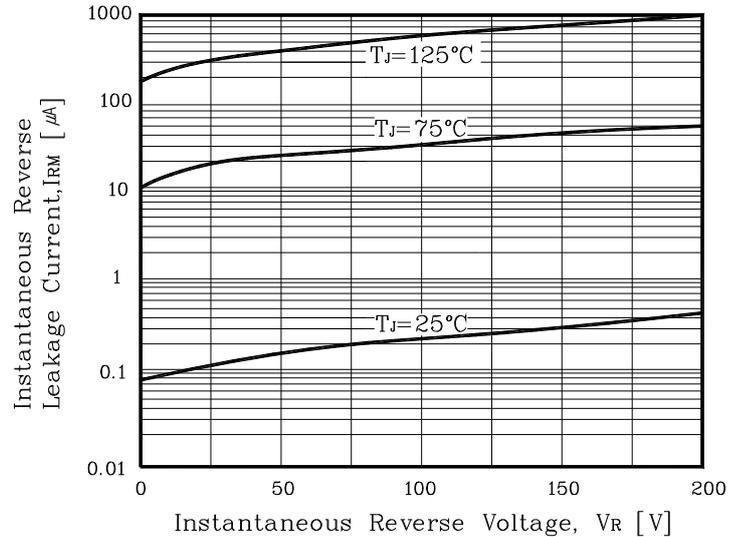
Fig. 3) Maximum Forward Derative Curve

Average Forward Rectified Current, $I_{F(AV)}$ [A] vs Case Temperature, T_C [°C]

$R_{th}(j-a) = R_{th}(j-c)$

Fig. 4) Forward Power Dissipation

Forward Power Dissipation, P_F [W] vs Average Forward Rectified Current, $I_{F(AV)}$ [A]

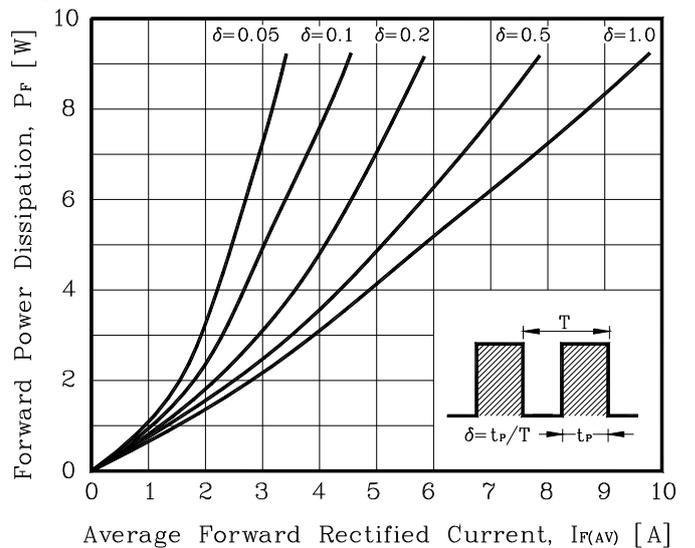$\delta=0.05$ $\delta=0.1$ $\delta=0.2$ $\delta=0.5$ $\delta=1.0$

$\delta=t_P/T$
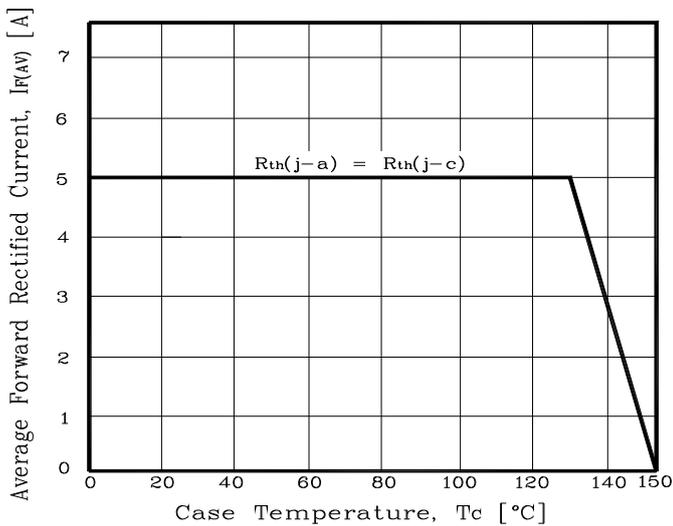
Fig. 5) Maximum Non-Repetitive Peak Forward Surge Current

Peak Forward Surge Current, I_{FSM} [A] vs Number of Cycle

8.3ms SINGLE HALF SINE WAVE (JEDEC METHOD)
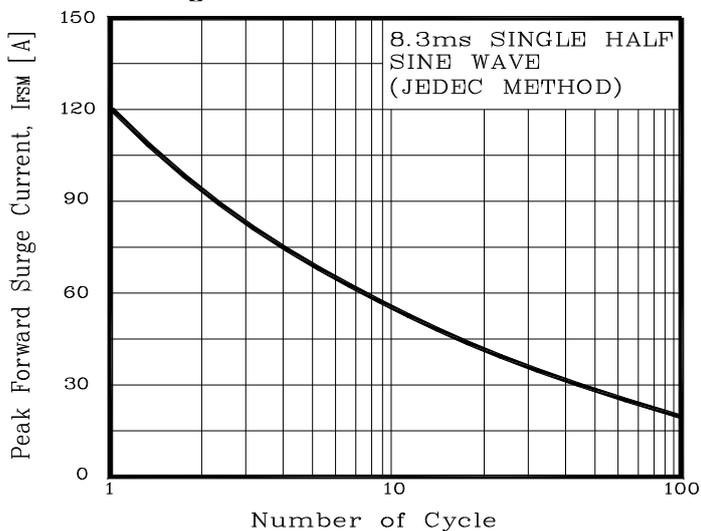
Fig. 6) Typical Junction Capacitance

Total capacitance C_T [pF] vs Reverse voltage V_R [V]

$f=1MHz$
$T_C=25°C$
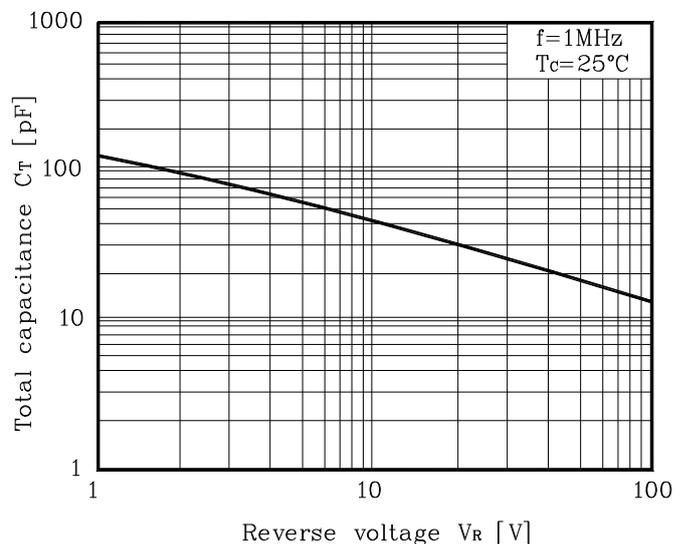
Package Outline Dimension
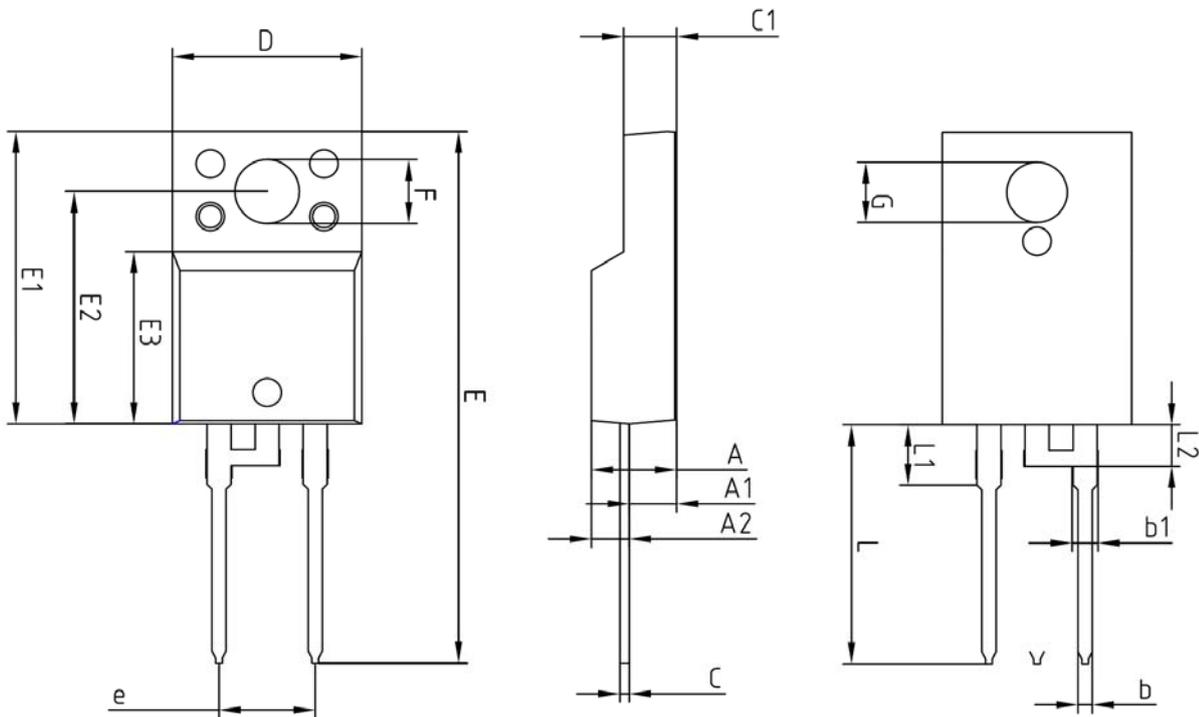
SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	−	−	4.60	
A1	2.45	2.50	2.55	
A2	1.95	2.00	2.05	
b	0.65	0.75	0.85	
b1	1.07	1.27	1.47	
C	0.40	0.50	0.60	
C1	2.70	2.80	2.90	
D	9.90	10.00	10.10	
E	28.00	−	28.60	
E1	15.50	15.60	15.70	
E2	12.30	12.40	12.50	
E3	9.15	9.20	9.25	
F	3.30	3.40	3.50	
G	3.10	3.20	3.30	
e	5.08 BSC			
L	12.40	−	13.00	
L1	3.46 BSC			
L2	2.21 BSC			